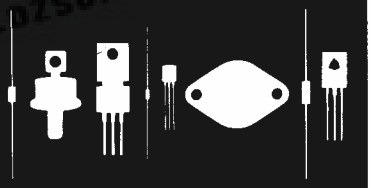
Central Semiconductor
Central Semiconductor™
148-B Lamar Street
West Babylon, New York 11704



SE9400
SE9401
SE9402

Silicon PNP Transistor

Darlington Power

JEDEC TO-220 Case

DESCRIPTION

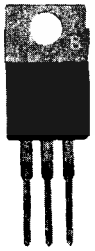
The CENTRAL SEMICONDUCTOR SE9400, 01, 02 are Silicon PNP Epitaxial Base, Monolithic Diffused Resistor Type Darlington Construction Power Transistors designed for audio amplifiers and medium power linear and switching applications.

MAXIMUM RATINGS (T_C=25°C)

		9400	9401	9402
Collector to Emitter Voltage	V_{CEO}	60V	80V	100V
Collector to Base Voltage	V_{CBO}	60V	80V	100V
Emitter to Base Voltage	V_{EBO}	5V	5V	5V
Collector Current	I_C	10A	10A	10A
Power Dissipation	P_D	70W	70W	70W
Operating Junction Temperature	T_J		-65 to +150°C	
Storage Temperature	T_{stg}		-65 to +150°C	

ELECTRICAL CHARACTERISTICS (T_C=25°C)

Symbol	Test Conditions		Min.	Max.	Unit
I_{CBO}	V_{CE}=Rated V_{CEO}			200	uA
I_{EBO}	V_{EB}=5.0V			4.0	mA
I_{CEO}	V_{CE}=0.5xRated V_{CEO}			500	uA
V_{CEO}	I_C=100mA	9400	60		V
		9401	80		V
		9402	100		V
$V_{CE(S)}$	I_C=4.0A, I_B=16mA			2.0	V
$V_{CE(S)}$	I_C=7.5A, I_B=150mA			2.5	V
$V_{BE(ON)}$	V_{CE}=3.0V, I_C=4.0A			2.5	V
$V_{BE(ON)}$	V_{CE}=3.0V, I_C=7.5A			3.0	V
h_{FE}	V_{CE}=3.0V, I_C=1.0A		750		-
h_{FE}	V_{CE}=3.0V, I_C=4.0A		1,000		-
h_{FE}	V_{CE}=3.0V, I_C=7.5A		100		-
h_{fe}	V_{CE}=3.0V, I_C=4.0A, f=1.0MHz		1.0		-



TO-220

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